

What is claimed is:

1. A fabricating method of a liquid crystal display, comprising the steps of:  
inserting a first substrate into a chamber to perform a dry etching process;  
removing the first substrate from the chamber after completion of the dry etching process;  
inserting a dummy substrate into the chamber;  
injecting inert gas into the chamber to eliminate a process byproduct and a remaining gas;  
taking the dummy substrate out from the chamber; and  
inserting a second substrate into the chamber having the process byproduct and the remaining gas removed, to perform an ashing process.
2. The fabricating method according to claim 1, wherein the step of performing the dry etching process includes:  
dry-etching a gate metal layer that is deposited on the first substrate.
3. The fabricating method according to claim 1, wherein the step of performing the dry etching process includes:  
dry-etching a protective film that is deposited on the first substrate.
4. The fabricating method according to claim 1, wherein the inert gas includes helium gas He.

5. The fabricating method according to claim 1, wherein the step of performing the ashing process includes:

making a photo resist pattern thinner, wherein the photo resist pattern is formed on the second substrate.

6. The fabricating method according to claim 5, wherein the photo resist pattern overlaps a channel part of a thin film transistor formed on the second substrate.

7. The fabricating method according to claim 1, wherein the step of performing the ashing process is performed using an ashing gas injected into the chamber, the ashing gas includes SF<sub>6</sub> gas and O<sub>2</sub> gas.

8. The fabricating method according to claim 7, wherein a SF<sub>6</sub> gas to O<sub>2</sub> gas ratio is 1:20.